Ordering number : ENN8147

SANYO Semiconductors
DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

2SK3820 — General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- 4V drive.
- Ultrahigh-speed switching.
- Motor drive, DC / DC converter.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		100	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		26	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	104	A
Allowable Power Dissipation	P_D		1.65	W
		Tc=25°C	50	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E_{AS}		84.5	mJ
Avalanche Current *2	I_{AV}		26	A

Note : *1 V_{DD}=20V, L=200μH, I_{AV}=26A
*2 L≤200μH, single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	100			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}= ±16V, V_{DS}=0V			±10	μA
Cutoff Voltage	$V_{GS}(off)$	V_{DS}=10V, I_D=1mA	1.2		2.6	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=10V, I_D=13A	11	19		S
Static Drain-to-Source On-State Resistance	$R_{DS}(on)1$	I_D=13A, V_{GS}=10V		45	60	mΩ
	$R_{DS}(on)2$	I_D=13A, V_{GS}=4V		56	80	mΩ

Marking : K3820

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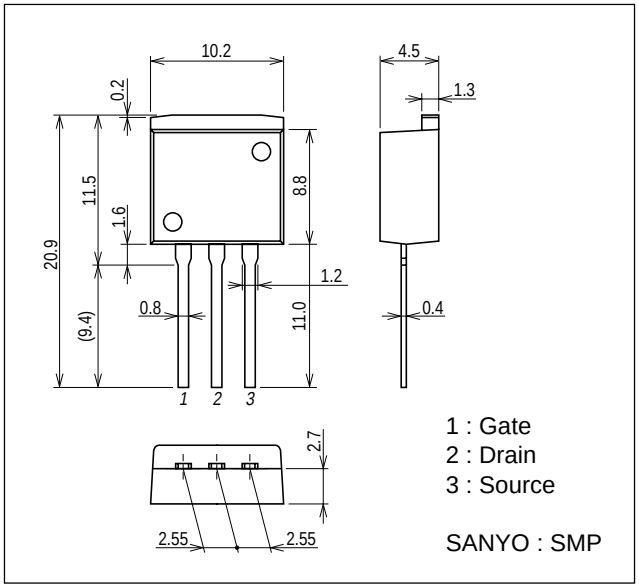
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		2150		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		160		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		110		pF
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit.		20		ns
Rise Time	t_{r}	See specified Test Circuit.		34		ns
Turn-OFF Delay Time	t_{d}(off)	See specified Test Circuit.		185		ns
Fall Time	t_{f}	See specified Test Circuit.		62		ns
Total Gate Charge	Qg	V_{DS}=50V, V_{GS}=10V, I_{D}=26A		44		nC
Gate-to-Source Charge	Qgs	V_{DS}=50V, V_{GS}=10V, I_{D}=26A		7.8		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=50V, V_{GS}=10V, I_{D}=26A		9.8		nC
Diode Forward Voltage	V_{SD}	I_{S}=26A, V_{GS}=0V		1.0	1.2	V

Package Dimensions

unit : mm

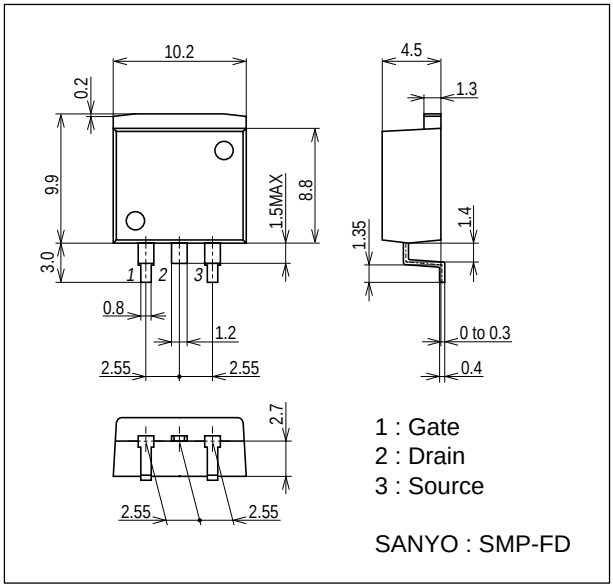
7513-002



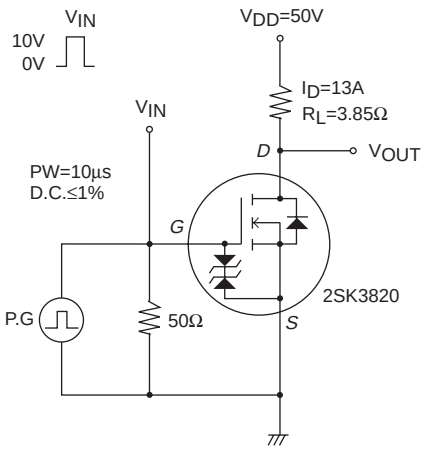
Package Dimensions

unit : mm

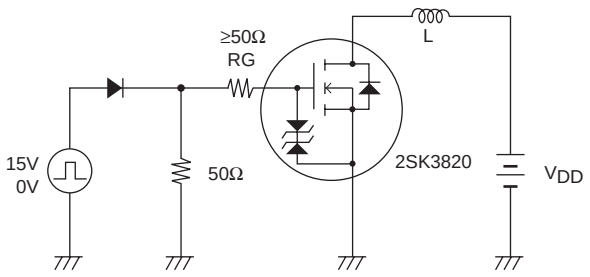
7001-003

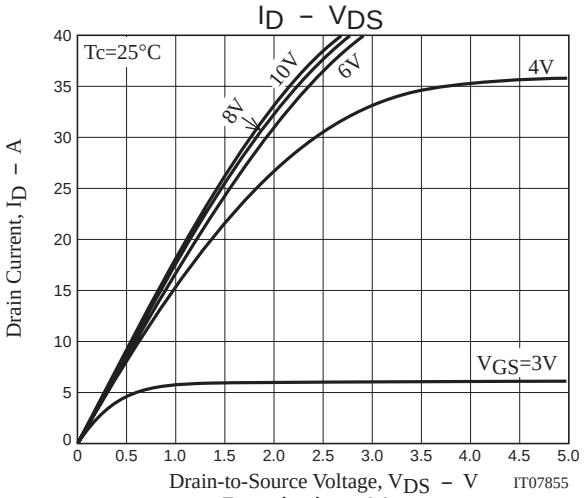


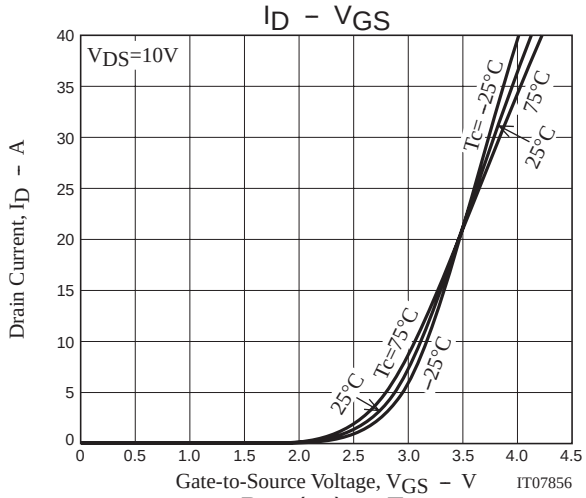
Switching Time Test Circuit

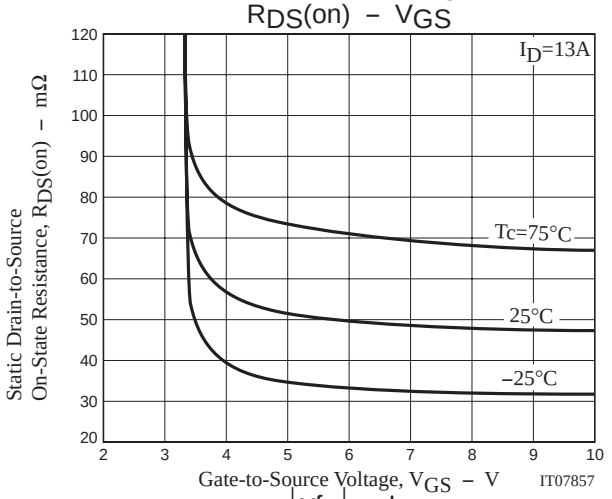


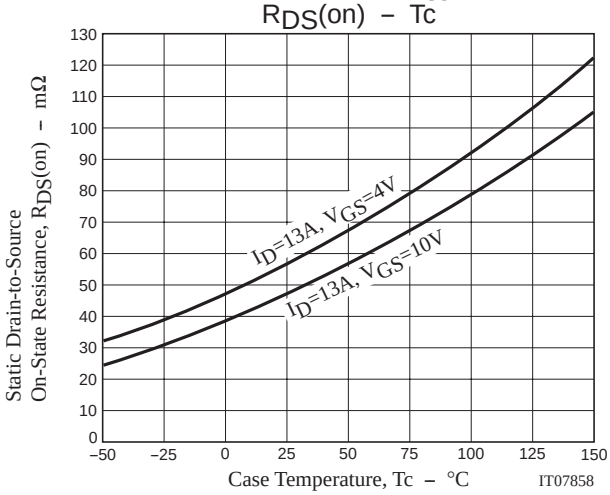
Unclamped Inductive Test Circuit

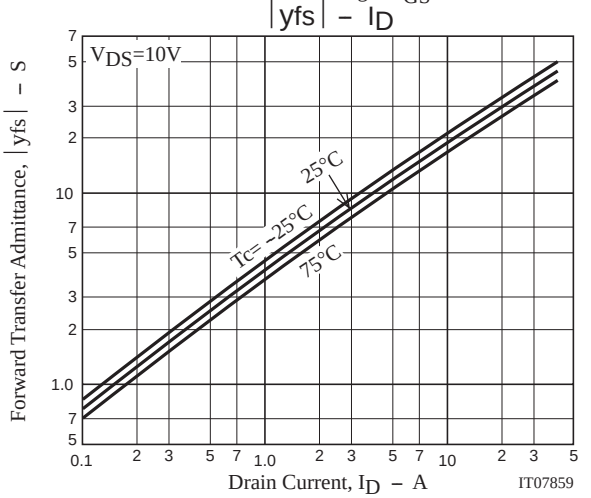


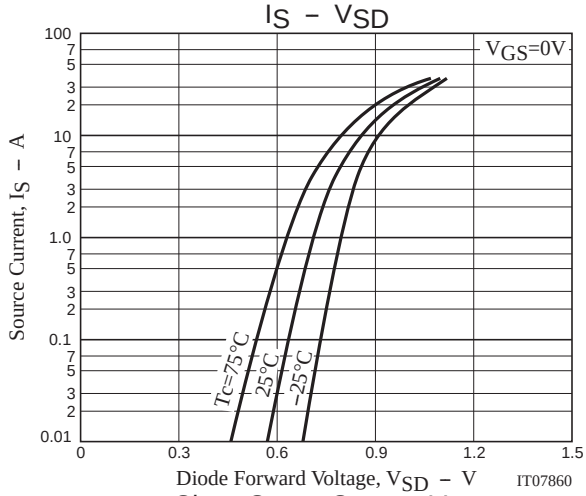

ID – VDS
Tc=25°C
8V
10V
6V
4V
VGS=3V
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT07855

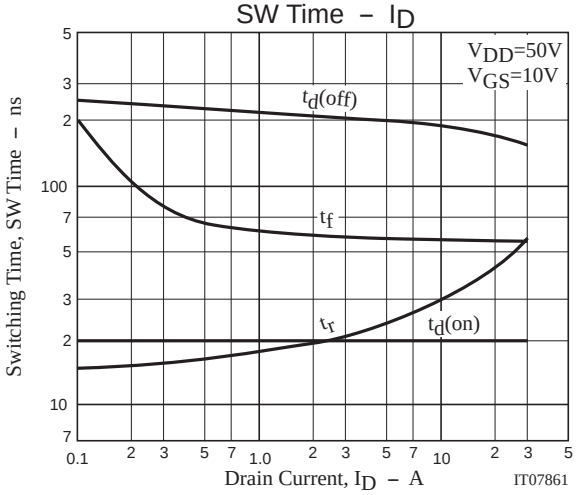

ID – VGS
VDS=10V
Tc= –25°C
75°C
25°C
25°C
Tc=75°C
–25°C
Drain Current, ID – A
Gate-to-Source Voltage, VGS – V
IT07856

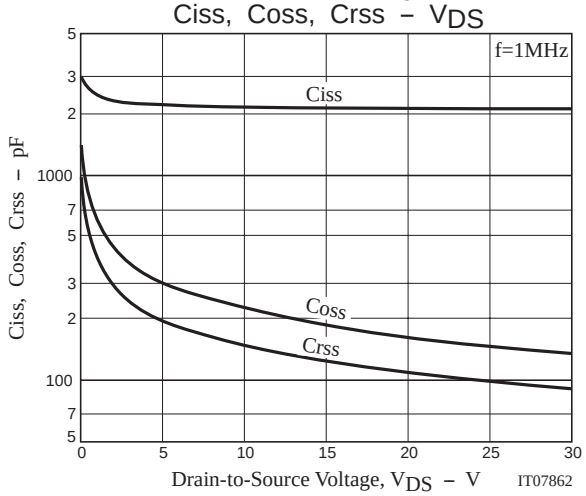

RDS(on) – VGS
ID=13A
Tc=75°C
25°C
–25°C
Static Drain-to-Source
On-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage, VGS – V
IT07857

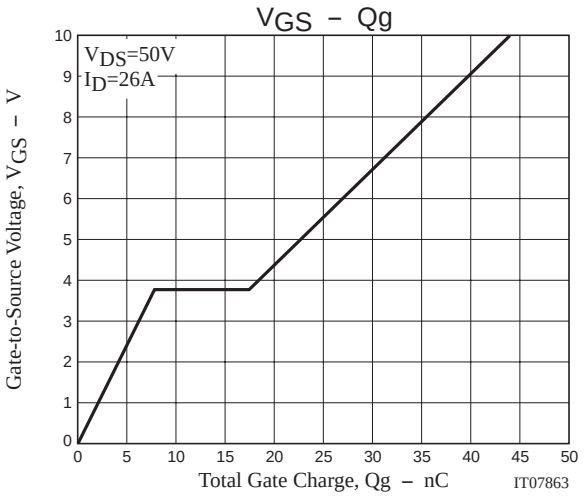

RDS(on) – Tc
ID=13A, VGS=4V
ID=13A, VGS=10V
Static Drain-to-Source
On-State Resistance, RDS(on) – mΩ
Case Temperature, Tc – °C
IT07858

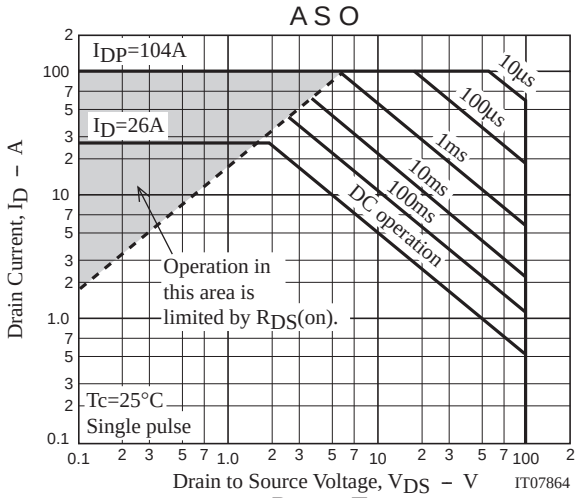

|yfs| – ID
VDS=10V
25°C
Tc= –25°C
75°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT07859

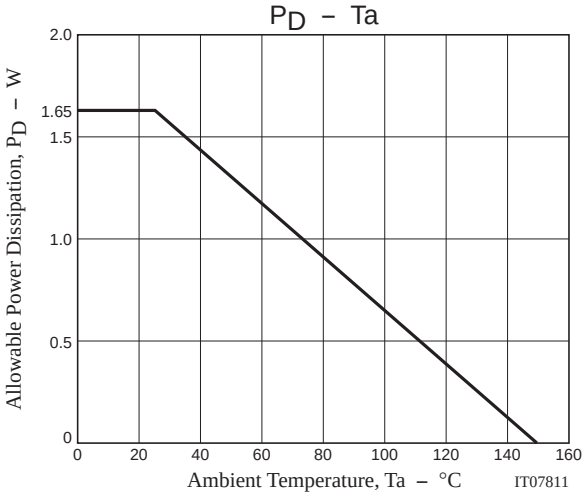

IS – VSD
VGS=0V
Tc=75°C
25°C
–25°C
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT07860

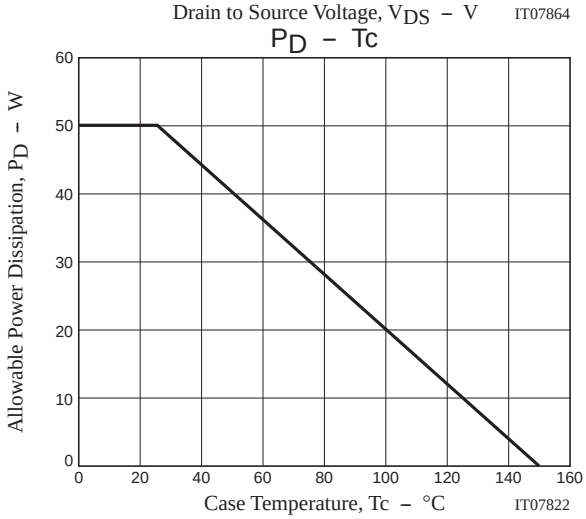

SW Time – ID
VDD=50V
VGS=10V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT07861


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT07862









Note on usage : Since the 2SK3820 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.